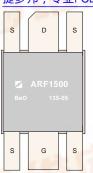
查询ARF1501供应商



## RF POWER MOSFET

### N-CHANNEL ENHANCEMENT MODE

专业PCB打样工厂,24小时加急出货



# **ARF1501**



250V

1500W 40MHz

The ARF1501 is an RF power transistor designed for very high power scientific, commercial, medical and industrial RF power generator and amplifier applications up to 40 MHz.

- Specified 300 Volt, 27.12 MHz Characteristics:
  - Output Power = 900 Watts.

Gain = 17dB (Class C)

Efficiency > 75%

- High Performance Power RF Package.
- Very High Breakdown for Improved Ruggedness.
- Low Thermal Resistance.
- Nitride Passivated Die for Improved Reliability.

#### **MAXIMUM RATINGS**

All Ratings: T<sub>C</sub> = 25°C unless otherwise specified.

Symbol	Parameter	ARF 1500	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	1000	Volts	
$V_{DGO}$	Drain-Gate Voltage	1000		
I <sub>D</sub>	Continuous Drain Current @ T <sub>C</sub> = 25°C	30	Amps	
V <sub>GS</sub>	Gate-Source Voltage	±30	Volts	
P <sub>D</sub>	Total Device Dissipation @ T <sub>C</sub> = 25°C	1500	Watts	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 200		
T <sub>L</sub>	Lead Temperature: 0.063" from Case for 10 Sec.	300	°C	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage (V <sub>GS</sub> = 0V, I <sub>D</sub> = 250 μA)	1000		\/alta		
V <sub>DS(ON)</sub>	On State Drain Voltage (ID(ON) = 15A, VGS = 10V)			9	Volts	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V)			100		
	Zero Gate Voltage Drain Current (V <sub>DS</sub> = 0.8 V <sub>DSS</sub> , V <sub>GS</sub> = 0V, T <sub>C</sub> = 125°C)		-7:74	1000	μΑ	
I <sub>GSS</sub>	Gate-Source Leakage Current (V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V)	2 (3)		±400	nA	
g <sub>fs</sub>	Forward Transconductance (V <sub>DS</sub> = 25V, I <sub>D</sub> = 12.5A)	3	5.3		mhos	
V <sub>isolation</sub>	RMS Voltage (60Hz Sinewave from terminals to mounting surface for 1 minute)	2500			Volts	
$V_{GS(TH)}$	Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50mA)	3		5	\ / II	
	FB T TSC.COM				Volts	

#### THERMAL CHARACTERISTICS

Symbol	Characteristic (per package unless otherwise noted)	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.12	°C/W
$R_{\theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planar Heat Sink Surface.)		0.09		C/VV

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - http://www.advancedpower.com

Phone: (541) 382-8028

#### **DYNAMIC CHARACTERISTICS**

#### **ARF1501**

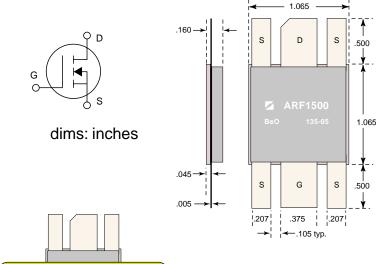
Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		3600	5900	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 150V		280	520	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		108	200	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 15V		7	15	
t <sub>r</sub>	Rise Time	$V_{DD} = 0.5 V_{DSS}$		5	10	ns
t <sub>d(off)</sub>	Turn-off Delay Time	I <sub>D</sub> = I <sub>D[Cont.]</sub> @ 25°C		23	40	113
t <sub>f</sub>	Fall Time	$R_{G}^{}$ = 1.6 $\Omega$		12	25	

#### **FUNCTIONAL CHARACTERISTICS**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
G <sub>PS</sub>	Common Source Amplifier Power Gain	f = 27.12 MHz	17	19		dB
η	Drain Efficiency	$V_{GS} = 0V$ $V_{DD} = 300V$	70	75		%
Ψ	Electrical Ruggedness VSWR 20:1	P <sub>out</sub> = 900W No Degradation in Output P				t Power

1 Pulse Test: Pulse width < 380 µS, Duty Cycle < 2%.

APT Reserves the right to change, without notice, the specifications and information contained herein.



Clamp

Compliant

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and mounting surface is beryllium oxide. Beryllium oxide dust is highly toxic when inhaled. Care must be taken during handling and mounting to avoid damage to this area. These devices must never be thrown away with general industrial or domestic waste.

Thermal Considerations and Package Mounting:

The rated 1500W power dissipation is only available when the package mounting surface is at 25°C and the junction temperature is 200°C. The thermal resistance between junctions and case mounting surface is 0.12 °C/W. When installed, an additional thermal impedance of 0.09 °C/W between the package base and the mounting surface is typical. Insure that the mounting surface is smooth and flat. Thermal joint compound must be used to reduce the effects of small surface irregularities. The heat-sink should incorporate a copper heat spreader to obtain best results.

The package is designed to be clamped to a heatsink. A clamped joint maintains the required mounting pressure while allowing for thermal expansion of both the device and the heat sink. A simple clamp, a compliant layer of plastic or rubber, and two 6-32 (M3.5) screws can provide the minimum 85 lb required mounting force. T = 6 in-lb.

Heat Sink